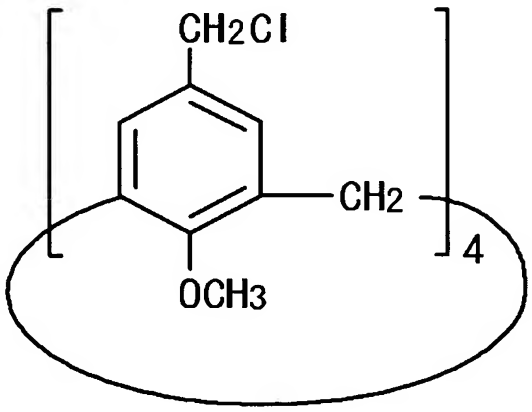
AMENDMENTS TO THE CLAIMS

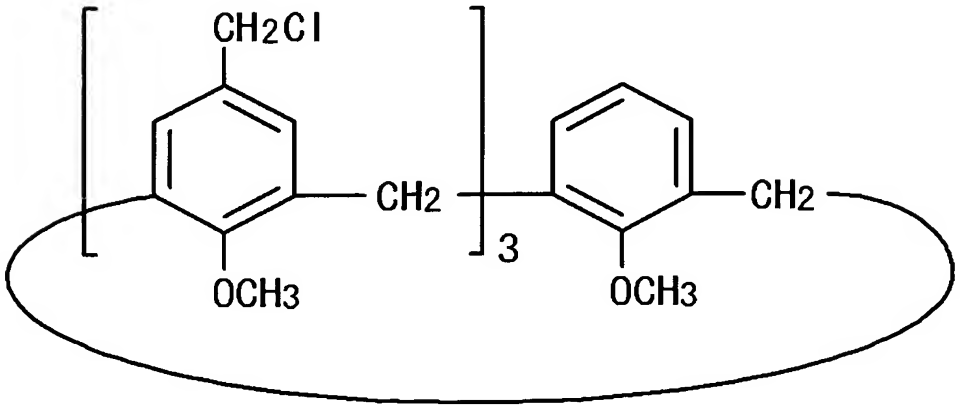
1. (Original) A calixarene composition comprising at least one of 5,11,17,23 - tetrachloromethyl – 25,26,27,28 – tetramethoxycalix [4] arene (CMC4AOMe) represented by the structural formula (I) of the following chemical formula 1 and 5,11,17 – trichloromethyl – 25,26,27,28 – tetramethoxycalix [4] arene (CMC3AOMe) represented by the structural formula (II) of the following chemical formula 2.

[Chemical Formula 1]



(I)

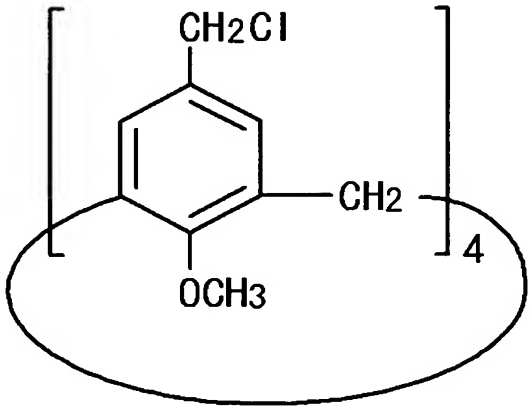
[Chemical Formula 2]



(II)

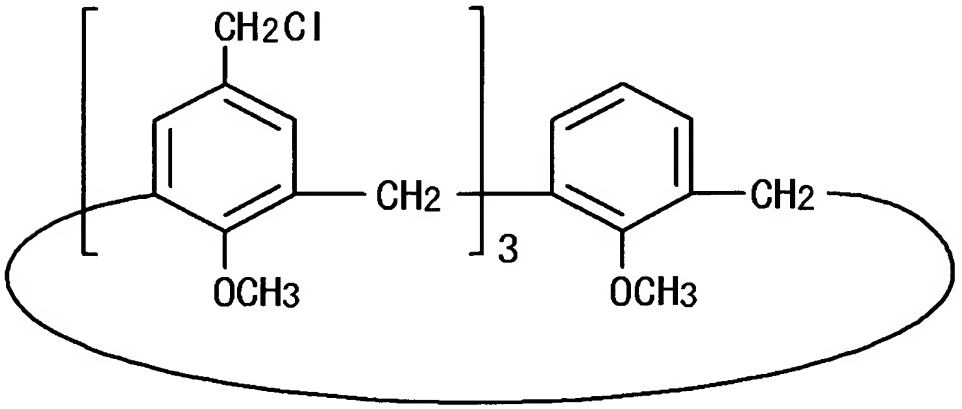
2. (Original) A resist comprising at least one of 5,11,17,23 - tetrachloromethyl – 25,26,27,28 – tetramethoxycalix [4] arene (CMC4AOMe) represented by the structural formula (I) of the following chemical formula 3 and 5,11,17 – trichloromethyl – 25,26,27,28 – tetramethoxycalix [4] arene (CMC3AOMe) represented by the structural formula (II) of the following chemical formula 4.

[Chemical Formula 3]



(I)

[Chemical Formula 4]

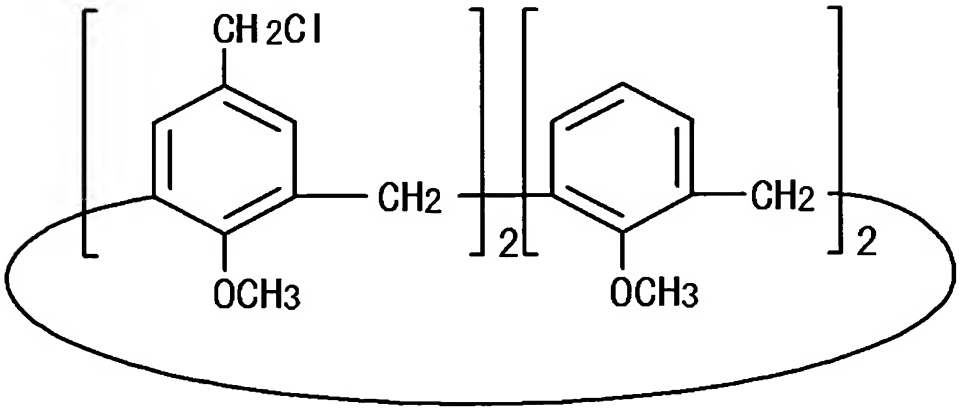


(II)

3. (Original) The resist according to claim 2, further comprising at least one of 5,11 – dichloromethyl – 25,26,27,28 – tetramethoxycalix [4] arene (CMC2AOMe) represented by the structural formula (III) of the following chemical formula 5 and 5 –

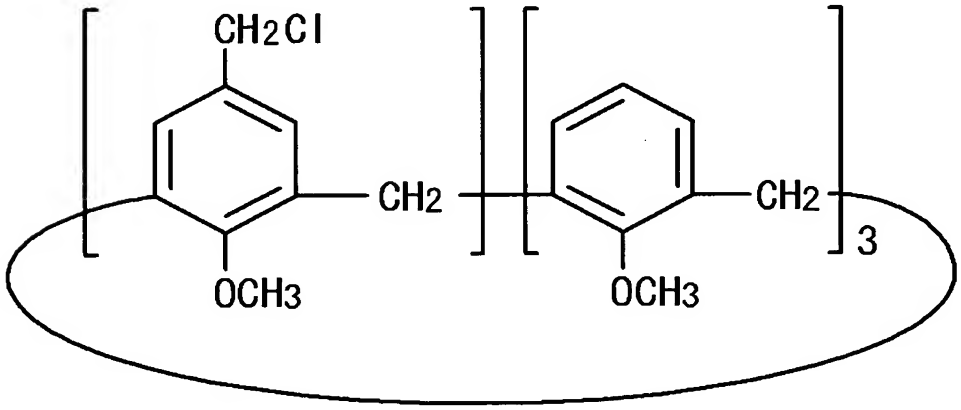
monochloromethyl – 25,26,27,28 – tetramethoxycalix [4] arene (CMC1AOMe) represented by the structural formula (IV) of the following chemical formula 6 is provided.

[Chemical Formula 5]



(III)

[Chemical Formula 6]



(IV)

4. (Currently Amended) The resist according to claim 2[[or 3]], further comprising at least one of oligomer and organic polymer compound.

5. (Currently Amended) The resist according to [[any one of claims 2 to 4]]claim 2, which is exposed by the irradiation of at least one of electronic beam, X-ray, ion beam and atomic beam.

6. (Currently Amended) The resist according to [[any one of claims 2 to 5]]claim 2, further comprising, at least one solvent selected from the group consisting of ethyl lactate (EL), propylene glycol monomethyl ether (PGME), propylene glycol monomethyl ether acetate (PGMEA), ethyl propionate, n-butyl acetate and 2-heptanone.

7. (Original) A method for forming a resist pattern comprising the following steps of coating the resist according to claim 6 on a substrate, exposing said resist to a radioactive ray; and a step developing said resist.

8. (Original) The method according to claim 7,

Wherein said radioactive ray is any of electronic beam, X-ray, ion beam and atomic beam.

9. (Currently Amended) The method according to claim 7[[or 8]],

wherein said developing step is carried out by using a developer comprising at least one selected from the group consisting of ethyl lactate (EL), propylene glycol monomethyl ether (PGME), propylene glycol monomethyl ether acetate (PGMEA), ethyl propionate, n-butyl acetate, 2-heptanone and tetramethyl ammonium hydroxide.

10. (Currently Amended) A method for hyperfine processing comprising the steps of forming a resist pattern using the resist pattern forming method according to [[any one of claims 7 to 9]]claim 7; and performing a processing on said substrate with said resist pattern as a mask.

11. (New) The resist according to claim 3, further comprising at least one of oligomer and organic polymer compound.